

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of
SOWLATI et al.

Atty. Docket
US-00.0099-A

Application No. 09/545,785

Group Art Unit: 2811

Filed: April 7, 2000

Examiner: Ori Nadav

For: INTERDIGITATED MULTILAYER CAPACITOR STRUCTURE FOR DEEP SUB-MICRON CMOS

#12 1/2
Suppl
Response
F Jones
5-3-02

AMENDMENT and/or RESPONSE under 37 C.F.R. § 1.111

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office action dated January 23, 2002,
please reconsider the application in light of the following remarks.

REMARKS

Claims 1-12 are pending in the application.

The Office action objects to the drawings under 37 CFR 1.84(p)(4), asserting that reference character "27" does not point to a dielectric layer located between conductive vias 30. Accordingly, applicants submit herewith a proposed drawing correction for FIG. 2B with reference characters 27, 28, and 29 more clearly pointing to respective dielectric layers as described in the disclosure. Accordingly, withdrawal of the objection to the drawings under 37 CFR 1.84(p)(4) is respectfully requested.

The Office action objects to the drawings under 37 CFR 1.84(a), stating that Fig. 2B "depicts dielectric layer comprising